

TRIUNE PRODUCTS

Features

- Supports standards (Qi®, PMA, A4WP) and proprietary wireless power applications
- Power outputs scalable based on FET size
- Support for half and full-bridge power sections
- Integrated demodulator amplifiers
- Low external component count
- Available in 28 pin 5x5 QFN

Applications

- Multi-standard compliant and non-compliant wireless chargers for:
 - Cell Phones and Smartphones
 - GPS Devices
 - Digital Cameras
 - Tablets and eReaders
- Full and half-bridge power converters
- Motor drive applications

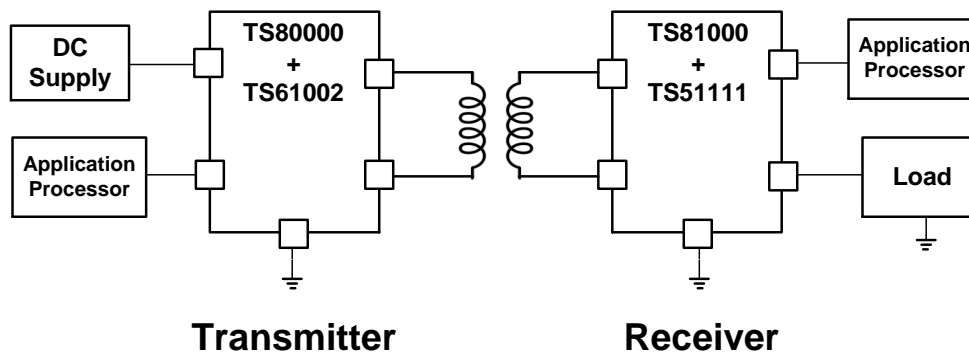
Description

TS61002 is a high-voltage FET driver that can be used to drive N-channel devices in full or half bridge configurations. TS61002 can support various power converter applications, multiple standard and proprietary wireless power applications, and motor driver systems.

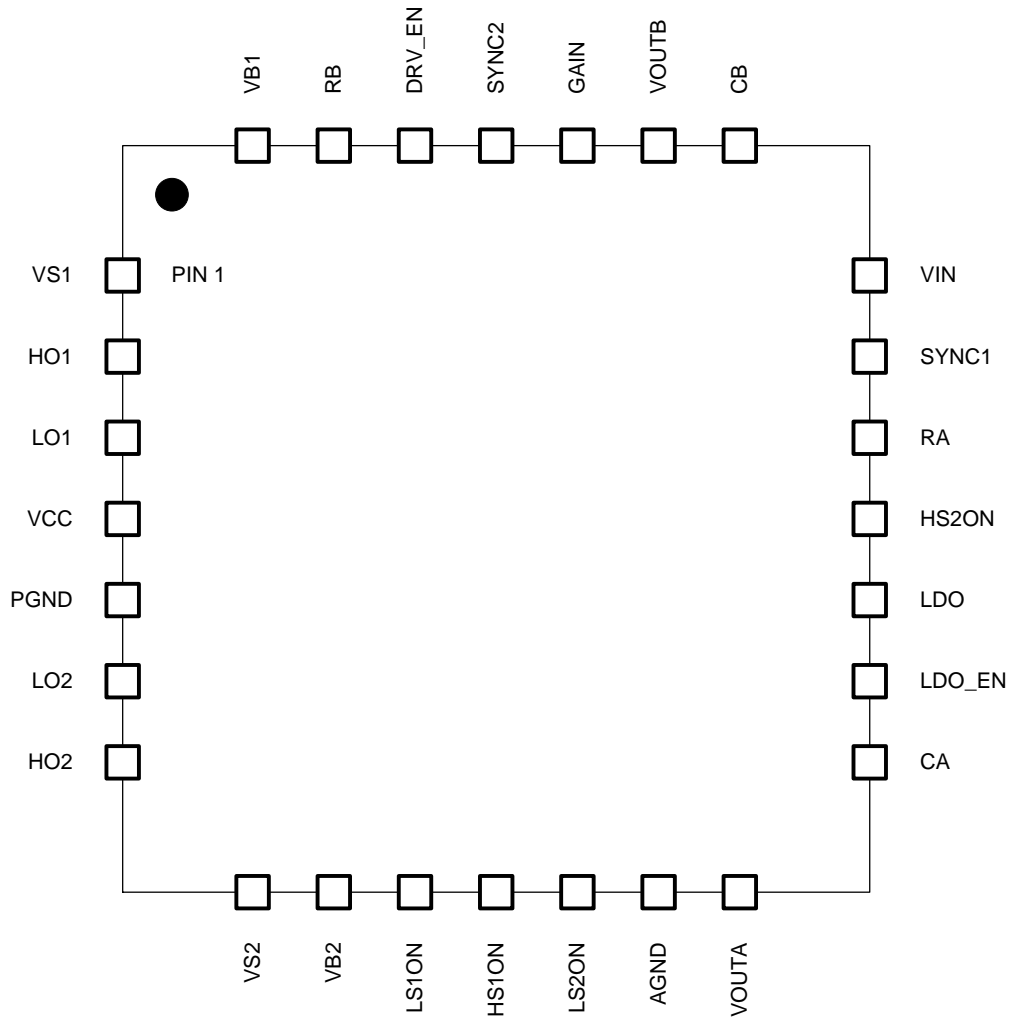
Specifications

- Drives both low side and high side N-channel MOSFETS
- 5Ω pull-up, 2Ω pull-down gate drivers
- Independent TTL compatible inputs
- Floating gate drive and bootstrap circuits for driving high side devices – up to 50V for the bridge supply voltage
- 5 V gate drive capability, down to 3.5V operation
- Fast propagation delays (<50ns~120ns typical)
- Matched channel to channel delays (<40ns mismatch typical)
- Fast rise and fall times
- Break before make detection to set minimum dead time protection
- Proprietary demodulator circuits for wireless power transmitter application
- High PSR 3.0V linear regulator (50mA capability) for supporting circuitry & external controller
- Under voltage lock out protection
- Over temperature shut down (TSD) protection

Typical Application Circuit



Pin Configuration

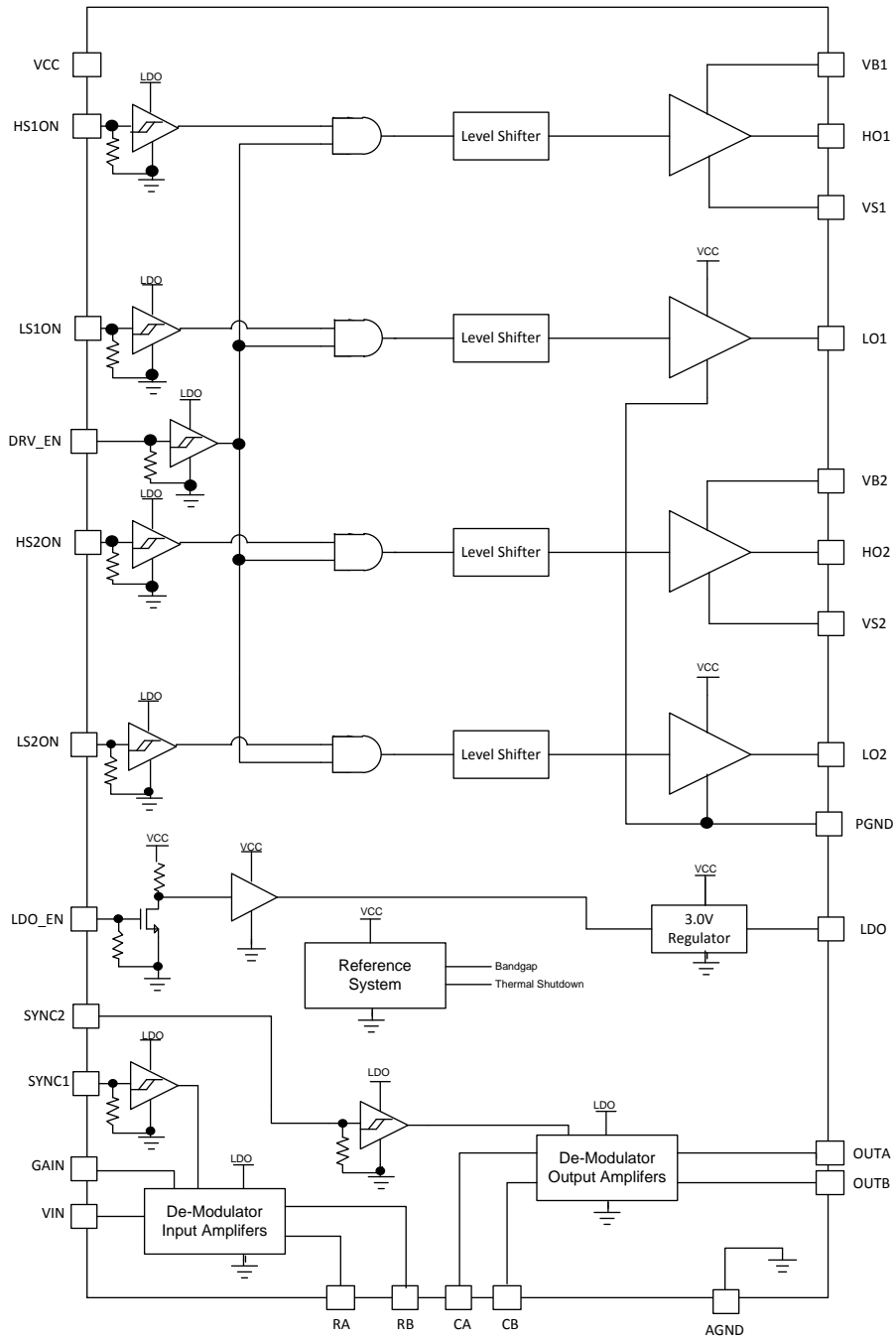


(Top View)

Pin Configuration

| QFN Pin # | Pin Symbol | Function | Description |
|-----------|------------|------------------------|--|
| 1 | VS1 | FET drive | High side MOSFET source #1 |
| 2 | HO1 | FET drive | High side MOSFET gate drive #1 |
| 3 | LO1 | FET drive | Low side MOSFET gate drive #1 |
| 4 | VCC | Gate drive input power | Input power supply (gate drive supply) |
| 5 | PGND | Power GND | Power GND |
| 6 | LO2 | FET drive | Low side MOSFET gate drive #2 |
| 7 | HO2 | FET drive | High side MOSFET gate drive #2 |
| 8 | VS2 | FET drive | High side MOSFET source #2 |
| 9 | VB2 | Bootstrap | Bootstrap for gate drive #2 |
| 10 | LS1ON | PWM1_L | Low-side gate control #1 with 30k Ω pull-down to GND |
| 11 | HS1ON | PWM1_H | High-side gate control #1 with 30k Ω pull-down to GND |
| 12 | LS2ON | PWM2_L | Low-side gate control #2 with 30k Ω pull-down to GND |
| 13 | AGND | Analog GND | Analog GND |
| 14 | VOUTA | Demodulator | Demodulator output A |
| 15 | CA | Demodulator | Demodulator input CA |
| 16 | LDO_EN | LDO enable | LDO enable (active high) with 30k Ω pull-down to GND |
| 17 | VLDO | LDO output | 3.0V regulator output and decoupling |
| 18 | HS2ON | PWM2_H | High-side gate control #2 with 30k Ω pull-down to GND |
| 19 | RA | Demodulator | Demodulator output RA |
| 20 | SYNC1 | Demodulator | Demodulator SYNC1 input with 30k Ω pull-down to GND |
| 21 | VIN | Demodulator | Demodulator input |
| 22 | CB | Demodulator | Demodulator input CB |
| 23 | VOUTB | Demodulator | Demodulator output B |
| 24 | GAIN | Demodulator | Demodulator input gain setting |
| 25 | SYNC2 | Demodulator | Demodulator SYNC2 input with 30k Ω pull-down to GND |
| 26 | DRV_EN | Gate drive enable | Gate drive enable (active high) with 30k Ω pull-down to GND |
| 27 | RB | Demodulator | Demodulator output RB |
| 28 | VB1 | Bootstrap | Bootstrap for gate drive #1 |

Functional Block Diagram



Absolute Maximum Ratings

Over operating free-air temperature range unless otherwise noted (1, 2)

| Parameter | Value | Unit |
|--|----------------------------|------|
| VCC, LO1, LO2 | 8.0 | V |
| VS1, VS2 | 50 | V |
| VB1, VB2, HO1, HO2 | 8.0 (relative to VS1, VS2) | V |
| LDO_EN | 8.0 | V |
| LS1ON, LS2ON, HS1ON, HS2ON, DRV_EN | 3.6 | V |
| VIN, GAIN, RA, RB, CA, CB, SYNC1, SYNC2, DRV_EN, VOUTA, VOUTB | 3.6 | V |
| Electrostatic Discharge – Human Body Model (VS1, HO1, LO1, VCC, PGND, LO2, HO2, VS2, VB2, HS1ON, AGND, LDO_EN, VB1) | +/-2k | V |
| Electrostatic Discharge – Human Body Model (LS1ON, LS2ON, VOUTA, CA, LDO, HS2ON, RA, SYNC1, VIN, CB, VOUTB, GAIN, SYNC2, DRV_EN, RB) | +/-1k | V |
| Electrostatic Discharge – Charge Device Model | +/-1k | V |
| Lead Temperature (soldering, 10 seconds) | 260 | °C |

- (1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to AGND.

Thermal Characteristics

| Symbol | Parameter | Value | Unit |
|--------------------|--|------------|------|
| θ_{JA} | Thermal Resistance Junction to Air (Note 1) | 25.7 | °C/W |
| θ_{JC} | Thermal Resistance Junction to Case (Note 1) | 1.84 | °C/W |
| T _{STG} | Storage Temperature Range | -65 to 150 | °C |
| T _{J,MAX} | Maximum Junction Temperature | 150 | °C |
| T _J | Operating Junction Temperature Range | -40 to 125 | °C |

Note 1: Assumes 28LD 5x5 QFN mounted on a 4-layers FR4 2S2P JEDEC board as per JESD51-7 with 13.5 inch² of 1 oz Cu and 9 thermal vias connected to PAD.

Recommended Operating Conditions

| Symbol | Parameter | Min | Typ | Max | Unit |
|---------------------|--|-----|-----|-----|------|
| VCC | Input Operating Voltage | 3.5 | 5 | 6 | V |
| VSx | Bridge Supply Voltage | 1.0 | 5 | 50 | V |
| C _{VCCBYP} | VCC Bypass Capacitor | | 10 | | μF |
| C _{3P3BYP} | Internal 3.0V Bypass Capacitor | | 4.7 | | μF |
| C _{BST} | Bootstrap Capacitor | | 47 | | nF |
| f _{PWL} | Maximum Gate Drive Switching Frequency | | | 300 | kHz |

Electrical Characteristics

$T^j = 25^\circ\text{C}$ for typical, $T^j = -40^\circ\text{C}$ to 125°C for min and max, $V_{CC} = 5\text{V}$, $V_S = 3.5\text{V} \sim 50\text{V}$ (unless otherwise noted)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|---|---|--|----------|------|----------|---------------|
| VCC Supply Voltage | | | | | | |
| VCC | Input Supply Voltage | | 3.5 | 5 | 6 | V |
| VS | Bridge supply Voltage | | 3.5 | 5.0 | 50 | V |
| Iq_ps | Input Supply current | LDO_EN = Hi; DRV_EN=0V; No load; LDO on, Gate drivers off, demodulator off | | 0.42 | 0.75 | mA |
| Iq_ps_drv | Input Supply current, drive mode, LDO_EN=Hi | LDO_EN & DRV_EN = Hi; LDO on, VIN=GAIN=0V, Gate driver Fs = 300KHz (no load), demodulator on | | 4 | 5.5 | mA |
| Iq_drv | Input Supply current, drive mode LDO_EN=0 | LDO_EN=VIN=GAIN=0V, external 3.0V on VLDO pin; DRV_EN=Hi; No load; Gate drivers on, demodulator on | | 1.8 | 3.0 | mA |
| Iqq_sleep | Stand by current | LDO_EN & DRV_EN= 0V; Inputs driven Low | | 1 | 10 | uA |
| Ron Characteristics | | | | | | |
| Ron (pulldown) | HS,LS pull down device | VCC = 5V | | 1.8 | 4 | Ω |
| Ron (pullup) | HS, LS pull up device | VCC = 5V | | 4.7 | 8.0 | Ω |
| Under Voltage Lock Out | | | | | | |
| UVLO (rise) | UV threshold (VCC) | Rising threshold measurement | 3.0 | 3.10 | 3.5 | V |
| UVLO (fall) | UV threshold (VCC) | Falling threshold measurement | 2.85 | 2.90 | 3.4 | V |
| Input Pins VIL, VIH & Pull-down Resistor | | | | | | |
| VIH | Digital Input Pins | Gate driver inputs, DRV_EN, SYNC1, SYNC2 | 0.7*VLDO | | VLDO | V |
| VIL | Digital Input Pins | Gate driver inputs, DRV_EN, SYNC1, SYNC2 | 0 | | 0.3*VLDO | V |
| LDOEN_VIH | VIH LDO_EN | Turn on VLDO | 1.5 | | VCC | V |
| LDOEN_VIL | VIL LDO_EN | Turn off VLDO | 0 | | 0.8 | V |
| Rpd | Pull-down resistors | Gate driver inputs, DRV_EN, LDO_EN, SYNC1, SYNC2 | 24 | 30 | 36 | k Ω |
| Gate Driver Power Up & Rise/Fall times | | | | | | |
| T _{suDRV_EN} | DRV_EN power up time ¹ | DRV_EN=1 to PWM gate driver ready, LDO_EN=0 mode (typical system latency = ~1ms) | | 20 | | μs |
| T _{r_LS} | Rise time (LS) | 1nF load; 20 – 80% | | 12 | | ns |
| T _{f_LS} | Fall time (LS) | 1nF load; 80 – 20% | | 12 | | ns |
| T _{r_HS} | Rise time (HS) | 1nF load wrt VSx; 20 – 80% | | 45 | | ns |
| T _{f_HS} | Fall time (HS) | 1nF load wrt VSx; 80 – 20% | | 10 | | ns |
| Propagation Delays, Cross Conduction Protection = ON, HSx/LSx Input Deadtime=0ns | | | | | | |
| T _{PLShl} | Prop delay (LS) high to low | LSxON to LOx (1V), 1nF load | | 50 | | ns |
| T _{PLShh} | Prop delay (LS) low to high | LSxON to LOx(1V), 1nF load | | 100 | | ns |
| T _{PHShl} | Prop delay (HS) high to low | HSxON to HOx (HOx – VSx = 1V), 1nF load wrt VSx | | 60 | | ns |
| T _{PHShh} | Prop delay (HS) low to high | HSxON to HOx (HOx – VSx = 1V), 1nF load wrt VSx | | 120 | | ns |
| T _{PMMlshs} | Prop delay mismatch (ls to hs) | LS off to HS on mismatch, 1nF load | | 15 | | ns |
| T _{PMMhsls} | Prop delay mismatch (hs to ls) | HS off to LS on mismatch, 1nF load | | 40 | | ns |
| TPW _{min} | Minimum pulse width response ¹ | | | 80 | | ns |
| 3.0V Regulator | | | | | | |
| Vout | Nominal Output voltage | | 2.70 | 3.0 | 3.30 | V |
| Iout | External loading | Output Current capability | 40 | 50 | | mA |
| Ilimit | Current Limit ¹ | VCC=3.5V, Iout when Vout shifts down10% | | 90 | | mA |

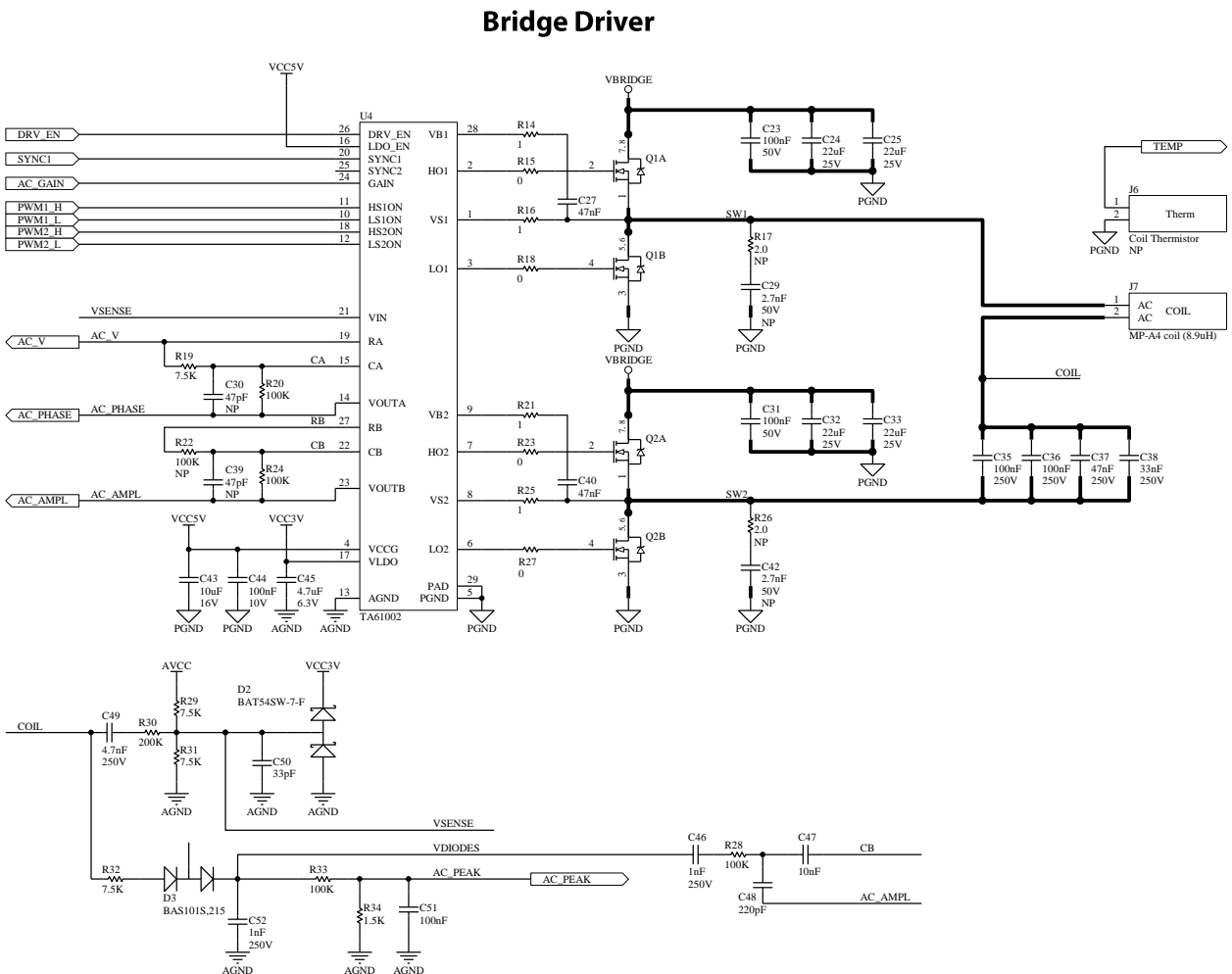
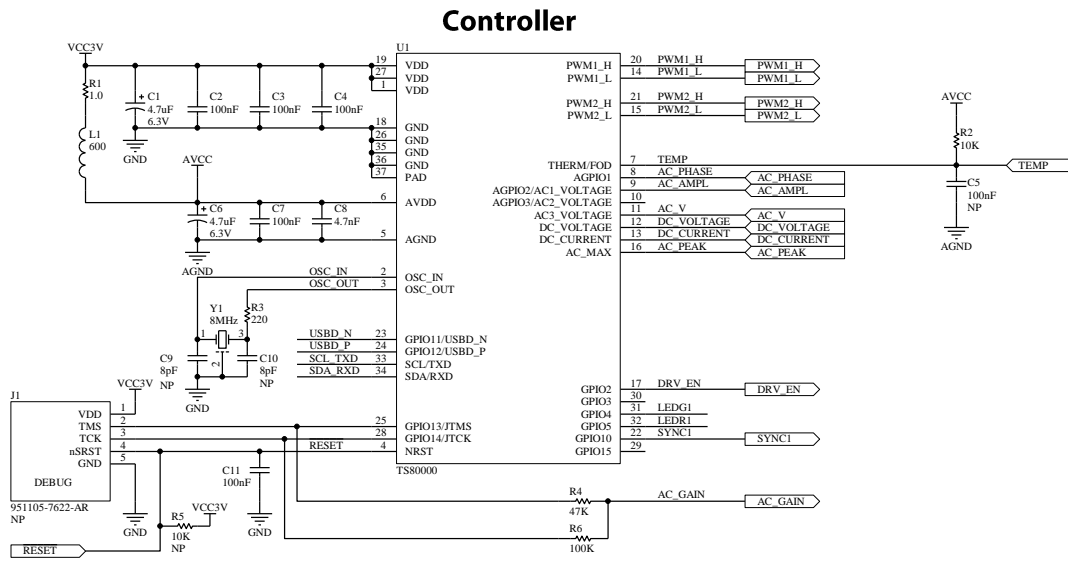
| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|--------------------|-------------------------------|--|------|------|------|------|
| Demodulator | | | | | | |
| Vinput | VIN, CA, CB pin input range | | 0.65 | | 2.35 | V |
| Av_VIN | VIN Input Gain Setting | 0dB | | 0.5 | | V |
| | | 6dB | | 1 | | V |
| | | 9.5dB | | 2 | | V |
| | | 12dB | | 2.5 | | V |
| RA_swing | RA Output Range | 100kΩ load to ground, 1Vpp input | 0.95 | 1.0 | 1.15 | Vpp |
| RB_swing | RB Output Range | 100kΩ load to ground, 1Vpp input | 0.35 | 0.42 | 0.55 | Vpp |
| VREF | Reference Voltage | VLDO=3.0V | | 1.5 | | V |
| VO | VOUTA, VOUTB Output Range | | 0 | | 3.0 | V |
| Trst | SYNC2 Reset Time ¹ | Capacitor between CB and VOUTB = 2.2nF | | 1.0 | | μs |

Note 1. Not tested in production

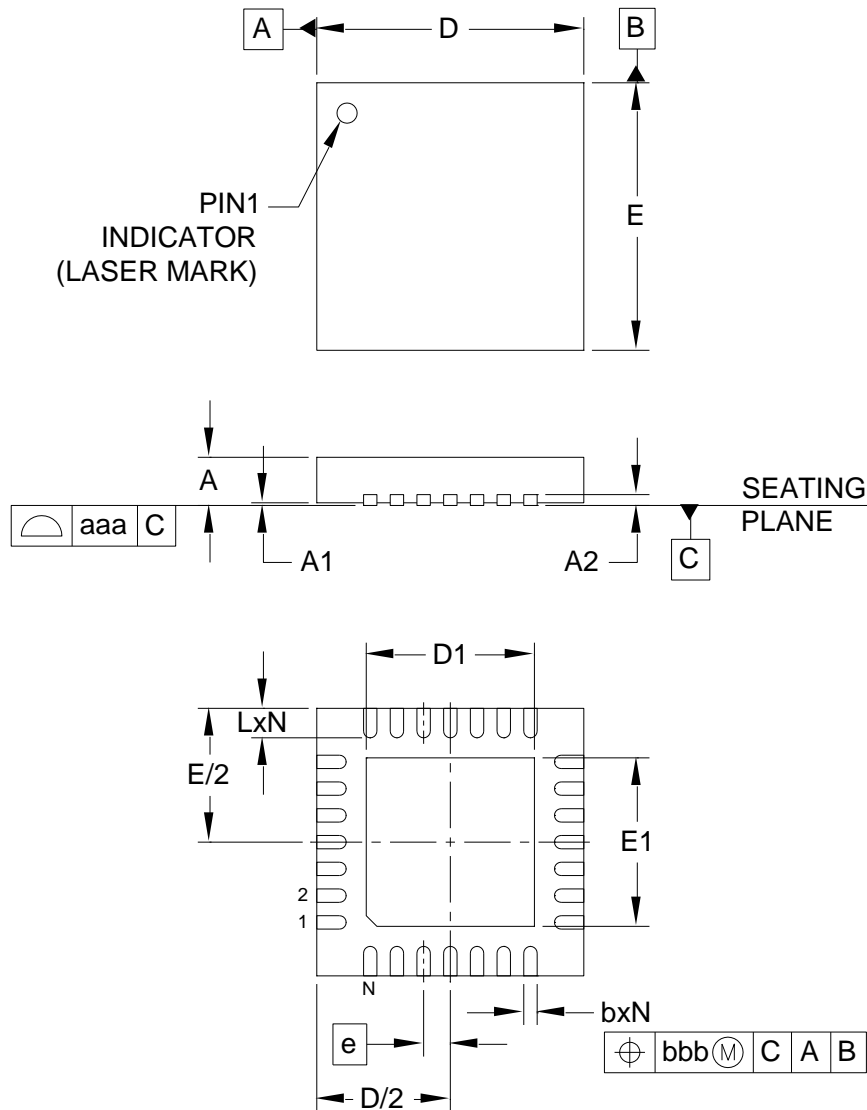
Operational Modes

| LDO_EN | DRV_EN | Operational Mode | Gate Drivers | Demodulator | LDO |
|--------|--------|------------------|--------------|-------------|-----|
| 0 | 0 | LDO=off, Idle | off | off | off |
| 0 | 1 | LDO=off, Drive | on | on | off |
| 1 | 0 | LDO=on, Idle | off | off | on |
| 1 | 1 | LDO=on, Drive | on | on | on |

Application Schematic



Package Drawing



| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN | NOM | MAX |
| A | 0.80 | - | 1.00 |
| A1 | 0.00 | - | 0.05 |
| A2 | (0.20) | | |
| b | 0.18 | 0.25 | 0.30 |
| D | 4.90 | 5.00 | 5.10 |
| D1 | 3.00 | 3.15 | 3.25 |
| E | 4.90 | 5.00 | 5.10 |
| E1 | 3.00 | 3.15 | 3.25 |
| e | 0.50 BSC | | |
| L | 0.45 | 0.55 | 0.65 |
| N | 28 | | |
| aaa | 0.08 | | |
| bbb | 0.10 | | |

NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

Ordering Information

| Device Part Number | Description |
|--------------------|------------------------|
| TS61002-QFNR | Full-bridge FET Driver |



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